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PATENT
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IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant:	Jun S. LEE	Conf.:	5244
Serial No.:	09/722,583	Art Unit:	2823
Filed:	November 28, 2000	Examiner:	B. Kebede
For:	METHOD FOR FABRICATING CAPACITOR OF SEMICONDUCTOR DEVICE		

SUPPLEMENTAL AMENDMENT UNDER 37 C.F.R. §1.111

Assistant Commissioner for Patents
Washington, DC 20231

February 5, 2003

Sir:

In response to the Office Action mailed November 7, 2002 (Paper No. 14), the following amendments and remarks are respectfully submitted in connection with the above-identified application:

IN THE CLAIMS:

Please **rewrite claims 1 and 4** as follows:

1. (Twice Amended) A method for fabricating a capacitor of a semiconductor device comprising:

depositing a nitride film and an oxide film over a substrate, the oxide film being deposited on the nitride film by chemical vapor deposition;

sequentially etching the oxide film and the nitride film using a patterned photoresist as a mask;